

FEATURES

Class AB linear GaAsFET hybrid design
Instantaneous wide bandwidth
Suitable for all modulations standards
Built-in protection circuits
High reliability and ruggedness

ELECTRICAL SPECIFICATIONS

Parameter	Specification	Notes
Operating Frequency Range	31.0 - 37.0 GHz	
Power Output	6 Watt Min	CW
Power Gain	38 dB Min	
Power Gain Flatness	4.0 dB p-p Max	Constant input power
Input / Output Return Loss	10 dB Min	Relative to 50 Ohm
Harmonics	>20 dBc Typ	At rated Pout
Non Harmonics Spurious	>60 dBc Min	
Operating Voltage	9.0 ± 0.5 VDC Nom	
Current Consumption	11.0 Amp Max	At rated Pout
Max Input Power	+5 dBm	Without damage
Load VSWR Protection	5 : 1	

ENVIRONMENTAL CHARACTERISTICS

Parameter	Specification	Notes
Operating Case Temperature	-20 to +65 °C	
Storage Temperature	-40 to +85 °C	
Relative Humidity	5 to 95 %	Non Condensation

MECHANICAL SPECIFICATIONS

Parameter	Specification	Notes
Dimensions	140 X 120 X 35 mm	Excluding Connectors
Weight	0.8Kg	
RF Connectors In/Out	K Type female/WR28	
DC Power / Interface Connector	9-Pin D-Sub	
Cooling	External Heatsink	Forced air required

D-SUB CONNECTOR PIN ASSIGNMENT

Pin	Function	Description
1	N/C	Reserved
2	N/C	Reserved
3	CURRENT SENSOR	I _D @20mV/100mA Typ
4	TEMP SENSOR	V _T @10mV/°C + 500mV Typ
5	SHUTDOWN	TTL
6,7	VDD	9VDC
8,9	GND	Ground

AMP3034 SOLID STATE HIGH POWER AMPLIFIER

OUTLINE DRAWING

